

AMENDMENTS TO THE SPECIFICATION:

Page 20, replace the paragraph, beginning on line 20, with the following amended paragraph:

--A plurality of openings reaching a silicon substrate (not shown) are formed in a silicon oxide 701 of the memory array region, and silicon plug 702 and titanium silicide 705 are packed into each of the openings. Crown structures 706 are formed at positions at which the crown structures are connected with titanium silicide 705 placed on silicon oxide 701.--

Page 28, replace the paragraph, beginning on line 21, with the following amended paragraph:

--Thereafter, on condition that sputtered ruthenium 1012 remains on the bottoms of the openings of crown structures 1011, the anisotropic dry etching is performed so as to remove ruthenium of crown surrounding region 1014 and makes ruthenium remain on the entire surface of crown structures 1011 including the head top portions of crown structures 1011 (FIG. 11N).--